

1 Electrical ratings

Symbol	Parameter		Value	— Unit
Symbol	Parameter	TO-220FP	TO-220FP I ² PAK, TO-220, IPAK	
V _{DS}	Drain-source voltage		600	
V _{GS}	Gate-source voltage		±25	V
1	Drain current (continuous) at T _C = 25 °C	11 ⁽¹⁾	11	•
Ι _D	Drain current (continuous) at T _C = 100 °C	6.9 ⁽¹⁾	6.9	— A
I _{DM} ⁽²⁾	Drain current pulsed	44(1)	44	Α
P _{TOT}	Total power dissipation at T_C = 25 °C	25 90		W
dv/dt ⁽³⁾	Peak diode recovery voltage slope		15	V/ns
V _{ISO}	Insulation withstand voltage (RMS) from all three leads to external heat sink (t = 1 s, T_C = 25 °C)	2.5		kV
TJ	Operating junction temperature range			°C
T _{stg}	Storage temperature range		-55 to 150	

Table 1. Absolute maximum ratings

1. Limited by maximum junction temperature.

2. Pulse width limited by safe operating area.

3. $I_{SD} \le 11 \text{ A}, \text{ di/dt} \le 400 \text{ A/}\mu\text{s}, V_{DD} = 80\% V_{(BR)DSS}.$

Table 2. Thermal data

Symbol	Parameter		Value		Unit
Symbol	r al allietei	TO-220FP	I²PAK, TO-220	IPAK	Unit
R _{thj-case}	Thermal resistance junction-case	5	5 1.39		°C/W
R _{thj-a}	Thermal resistance junction-ambient	62.5		100	°C/W

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I _{AS}	Avalanche current, repetitive or not repetitive (pulse width limited by T_J max)	3.5	A
E _{AS}	Single-pulse avalanche energy (starting T_J = 25 °C, I_D = I_{AS} , V_{DD} = 50 V)	200	mJ



2 Electrical characteristics

(T_C = 25 °C unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
V _{(BR)DSS}	Drain-source breakdown voltage	V _{GS} = 0 V, I _D = 1 mA	600			V
		V _{GS} = 0 V, V _{DS} = 600 V			1	
I _{DSS} Zero gate voltage drain curre	Zero gate voltage drain current	V_{GS} = 0 V, V_{DS} = 600 V, T_{C} = 125 °C ⁽¹⁾			100	μA
I _{GSS}	Gate-body leakage current	V_{DS} = 0 V, V_{GS} = ±25 V			±100	nA
V _{GS(th)}	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	2	3	4	V
R _{DS(on)}	Static drain-source on-resistance	V _{GS} = 10 V, I _D = 5.5 A		280	360	mΩ

Table 4. Static

1. Defined by design, not subject to production test.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
C _{iss}	Input capacitance		-	790	-	pF
C _{oss}	Output capacitance	V_{DS} = 50 V, f = 1 MHz, V_{GS} = 0 V	-	60	-	pF
C _{rss}	Reverse transfer capacitance		-	3.6	-	pF
C _{oss eq.} ⁽¹⁾	Equivalent output capacitance	V_{DS} = 0 to 480 V, V_{GS} = 0 V	-	135	-	pF
Qg	Total gate charge	V_{DD} = 480 V, I_D = 11 A, V_{GS} = 0 to 10 V (see Figure 17. Test circuit for gate		27	-	nC
Q _{gs}	Gate-source charge			4	-	nC
Q _{gd}	Gate-drain charge	charge behavior)	-	14	-	nC
Rg	Gate input resistance	f = 1 MHz, open drain	-	4.7	-	Ω

 C_{oss eq.} is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}.

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
t _{d(on)}	Turn-on delay time	V _{DD} = 300 V, I _D = 5.5 A,	-	3	-	ns
t _r	Rise time	R_G = 4.7 Ω , V_{GS} = 10 V	-	8	-	ns
t _{d(off)}	Turn-off delay time	(see Figure 16. Test circuit for resistive load switching times and	-	30	-	ns
t _f	Fall time	Figure 21. Switching time waveform)	-	10	-	ns

Table 7. Source-drain diode

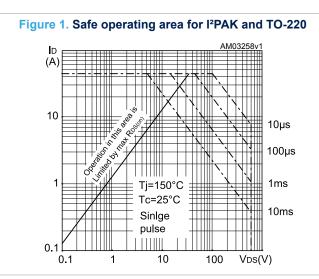
Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{SD}	Source-drain current		-		11	А
I _{SDM} ⁽¹⁾	Source-drain current (pulsed)		-		44	А
V _{SD} ⁽²⁾	Forward on voltage	V _{GS} = 0 V, I _{SD} = 11 A	-		1.5	V
t _{rr}	Reverse recovery time	I _{SD} = 11 A, di/dt = 100 A/µs,	-	230		ns
Q _{rr}	Reverse recovery charge	V _{DD} = 100 V	-	2		μC
I _{RRM}	Reverse recovery current	(see Figure 18. Test circuit for inductive load switching and diode recovery times)	-	18		А
t _{rr}	Reverse recovery time	I _{SD} = 11 A, di/dt = 100 A/µs,	-	290		ns
Qrr	Reverse recovery charge	V _{DD} = 100 V, T _J = 150 °C	-	2.5		μC
I _{RRM}	Reverse recovery current	(see Figure 18. Test circuit for inductive load switching and diode recovery times)	-	17		А

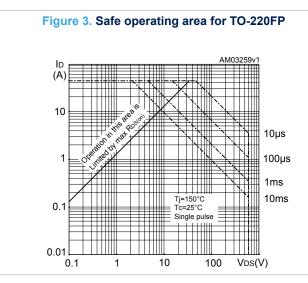
1. Pulse width is limited by safe operating area.

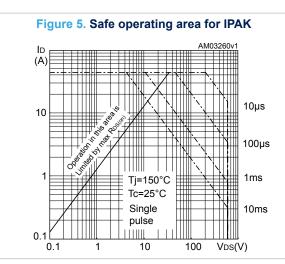
2. Pulse test: pulse duration = $300 \ \mu$ s, duty cycle 1.5%.

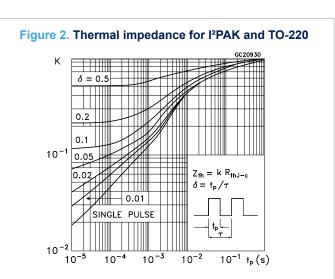


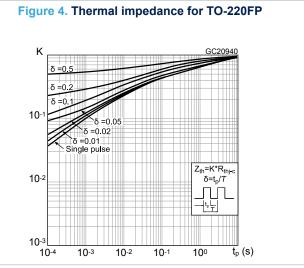
2.1 Electrical characteristics (curves)

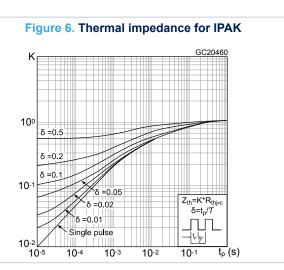




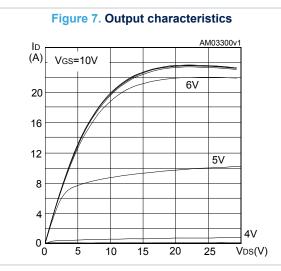


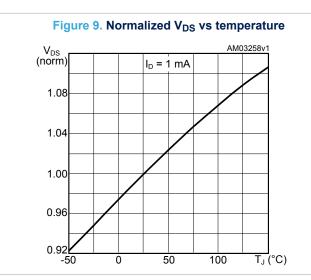


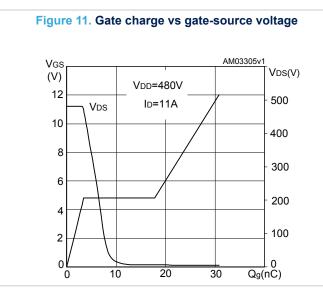












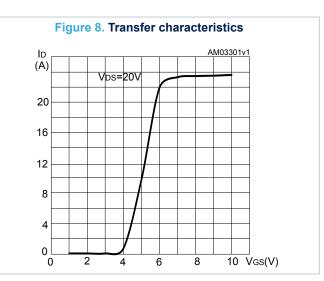
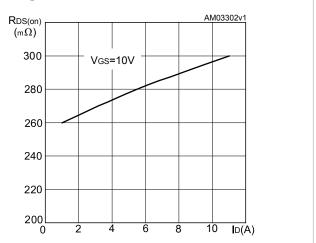
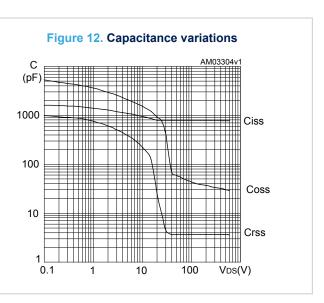
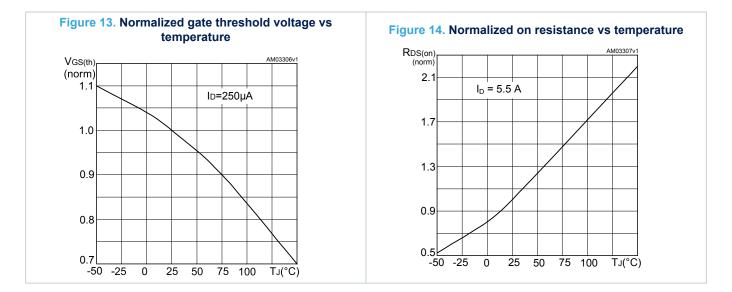


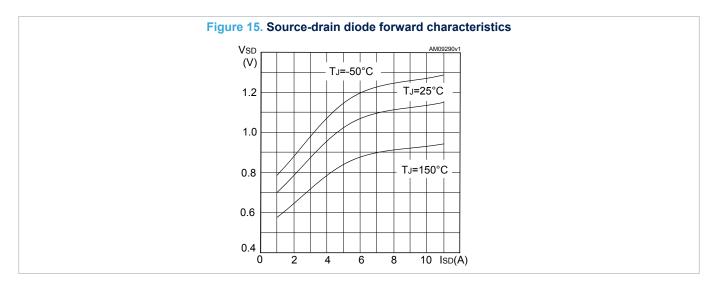
Figure 10. Static drain-source on-resistance





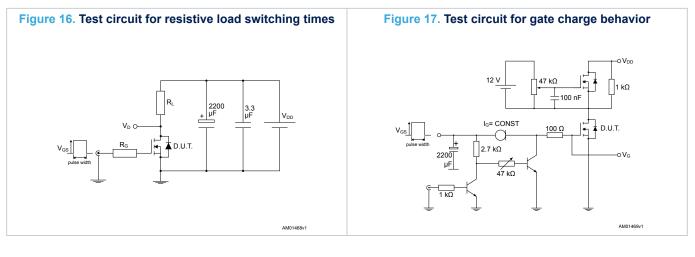


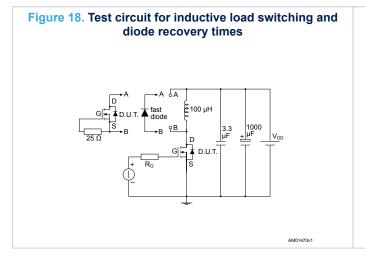


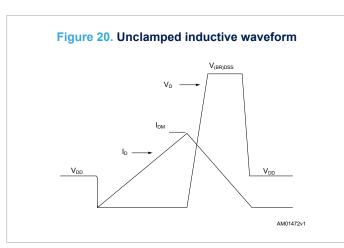


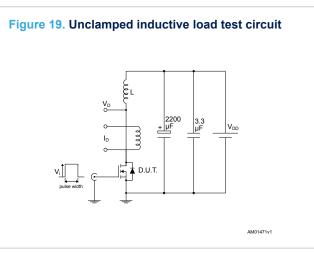


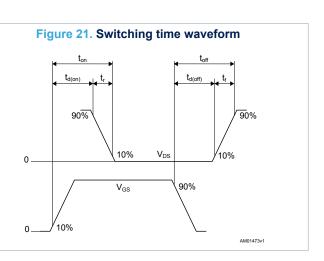
3 Test circuits











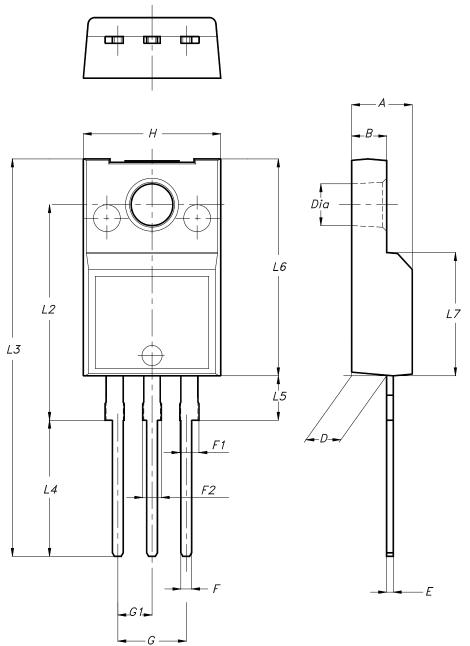


4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 TO-220FP package information





7012510_Rev_13_B



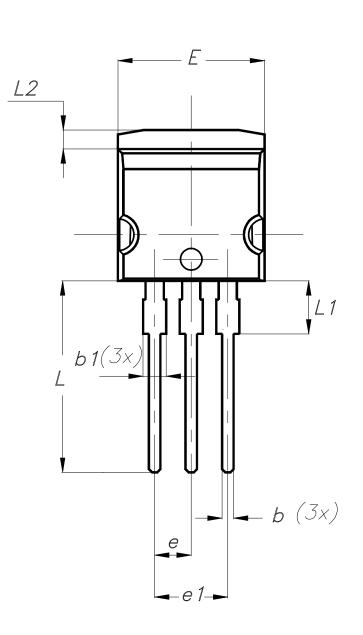
Dim.	mm			
Dim.	Min.	Тур.	Max.	
A	4.40		4.60	
В	2.50		2.70	
D	2.50		2.75	
E	0.45		0.70	
F	0.75		1.00	
F1	1.15		1.70	
F2	1.15		1.70	
G	4.95		5.20	
G1	2.40		2.70	
Н	10.00		10.40	
L2		16.00		
L3	28.60		30.60	
L4	9.80		10.60	
L5	2.90		3.60	
L6	15.90		16.40	
L7	9.00		9.30	
Dia	3.00		3.20	

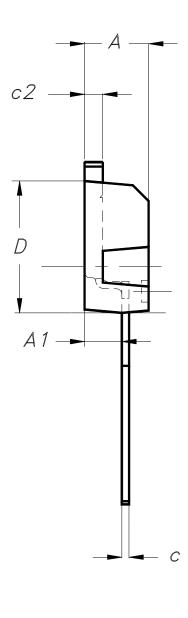
Table 8. TO-220FP package mechanical data



4.2 I²PAK package information

Figure 23. I²PAK package outline





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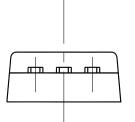
Table 9. I ² PAK package mechanical dat
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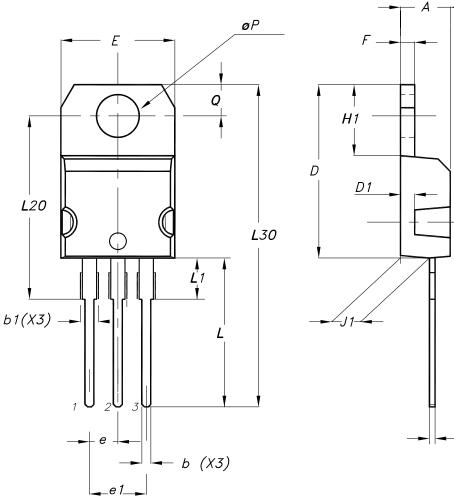
Dim.		mm	
Dini.	Min.	Тур.	Max.
A	4.40	-	4.60
A1	2.40	-	2.72
b	0.61	-	0.88
b1	1.14	-	1.70
С	0.49	-	0.70
c2	1.23	-	1.32
D	8.95	-	9.35
e	2.40	-	2.70
e1	4.95	-	5.15
Е	10.00	-	10.40
L	13.00	-	14.00
L1	3.50	-	3.93
L2	1.27	-	1.40



4.3 TO-220 type A package information

Figure 24. TO-220 type A package outline





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С



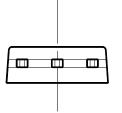
Dim.		mm	
Dim.	Min.	Тур.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.55
C	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10.00		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13.00		14.00
L1	3.50		3.93
L20		16.40	
L30		28.90	
øP	3.75		3.85
Q	2.65		2.95
Slug flatness		0.03	0.10

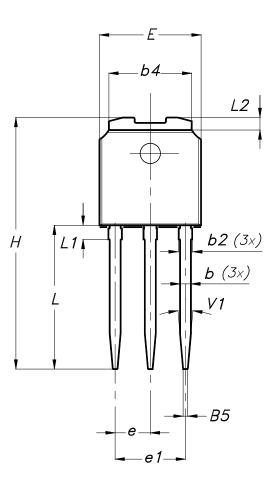
Table 10. TO-220 type A package mechanical data

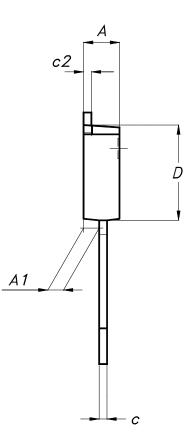


4.4 IPAK (TO-251) type A package information

Figure 25. IPAK (TO-251) type A package outline







0068771_IK_typeA_rev15

Dim.		mm	
Dim.	Min.	Тур.	Max.
А	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
B5		0.30	
С	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
е		2.28	
e1	4.40		4.60
Н		16.10	
L	9.00		9.40
L1	0.80		1.20
L2		0.80	1.00
V1		10°	

Table 11. IPAK (TO-251) type A package mechanical data



5 Ordering information

Table 12. Order codes

Order codes	Marking	Package	Packing
STF13NM60N		TO-220FP	Tube
STI13NM60N		I²PAK	
STP13NM60N	- 13NM60N	TO-220	
STU13NM60N		IPAK	



Revision history

Table 13. Document revision history

Date	Revision	Changes
29-Feb-2009	1	First release
13-Jan-2010	2	- Added new package, mechanical data: TO-247
		– Added new package, mechanical data: D ² PAK
08-Nov-2010	3	– Modified Figure 4
		– Added new package, mechanical data: I ² PAK
18-Jan-2012	4	– Added new package, mechanical data: IPAK
		– Minor text changes
14-Nov-2012	5	The part numbers STB13NM60N and STD13NM60N have been moved to a separate datasheet.
		Section 4: Package mechanical data has been updated.
26-Oct-2020	6	The part number STW13NM60N have been moved to a separate datasheet and the document has been updated accordingly.
		Updated cover page.
		Updated Section 1 Electrical ratings.
		Updated Table 4. Static and Table 7. Source-drain diode.
		Updated Section 4 Package information.
		Added Section 5 Ordering information.
		Minor text changes.



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Revi	evision history				



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